

NVHL080N120SC1

Silicon Carbide MOSFETN1200 V80 mΩTO247-3L



Silicon Carbide (SiC) MOSFET

EMI

- 1200V rated
 - Max RDS(on) = 110mΩ at Vgs = 20V, Id = 20A
 - High Speed Switching and Low Capacitance
 - 100% UIL Tested
 - Qualified for Automotive According to AEC-Q101
 - Devices are Pb-Free and are RoHS Compliant
- Typical RDS(on) = 80mΩ
- PFC
 - OBC
- Automotive DC/DC converter for EV/PHEV
 - Automotive On Board Charger
 - Automotive Auxiliary Motor Drive